

SSCN8050GS8

High Frequency High Gain NPN Power BJT

Features

VCB	VCE	VBE	IC
40V	25V	5V	500mA

> Description

This device is produced with advanced high carrier density technology, which is especially used to minimize saturation voltage drop. This device particularly suits low voltage applications such as portable equipment, power management and other battery powered circuits, and low in-line power dissipation are needed in a very small outline surface mount package. Excellent thermal and electrical capabilities.

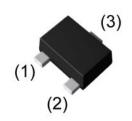
Applications

- Supply line switching circuits
- Battery management application
- DC/DC converter applications

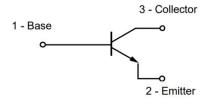
Ordering Information

Device	Package	Shipping
SSCN8050GS8	SOT-523	3000/Reel

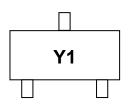
> Pin configuration



SOT-523



Circuit Diagram



Marking (Top View)





\succ Absolute Maximum Ratings (T_A=25 $^{\circ}$ C unless otherwise noted)

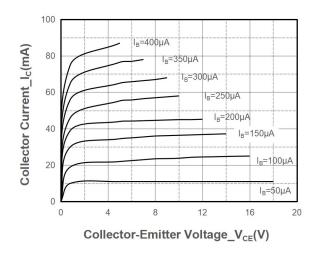
Parameter	Symbol	Value	Unit
Collector-Base Voltage	V _{CBO}	40	V
Collector- Emitter Voltage	V _{CEO}	25	V
Emitter-Base Voltage	V _{EBO}	5	V
Collector Current-Continuous	Ic	500	mA
Collector Power Dissipation	Pc	625	mW
Junction Temperature	TJ	150	°C
Storage Temperature	T _{STG}	-55 to 150	$^{\circ}$ C

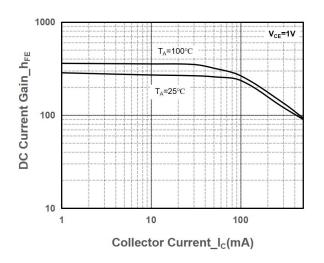
➤ Electrical Characteristics (T_A=25°C unless otherwise noted)

Parameter	Symbol	Test Conditions	Min.	Тур.	Max.	Unit
Collector-Base Breakdown Voltage	BV _{CBO}	$I_C=0.1$ mA, $I_E=0$	40			V
Collector-emitter Breakdown Voltage	BV _{CEO}	I _C =1mA,I _B =0	25			V
Emitter -Base Breakdown Voltage	BV _{EBO}	I _E =0.1mA,I _C =0	5			V
Collector Cutoff Current	I _{CBO}	V _{CB} =40V,I _E =0			0.1	μA
Emitter Cutoff Current	I _{EBO}	V _{EB} =5V,I _C =0			0.1	μA
DC Current Gain	h _{FE}	V _{CE} =1V,I _C =50mA	85		400	
Collector-Emitter Saturation Voltage	V _{CE(sat)}	I _C =500mA,I _B =50mA			0.6	V
Base-Emitter Saturation Voltage	V _{BE(sat)}	I _C =500mA,I _B =50mA			1.2	V
Townsition for more	f	V _{CE} =6V,I _C =20mA	150			MHz
Transition frequency	f _⊤	f=30MHz	150			IVITZ



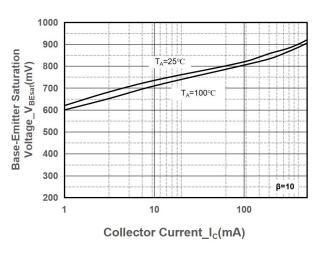
\succ Typical Performance Characteristics (T_A=25°C unless otherwise noted)

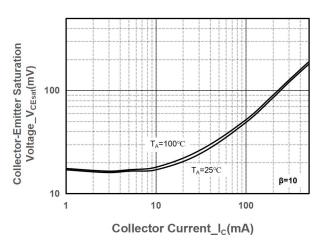




Collector Current vs. Collector-Emitter Voltage

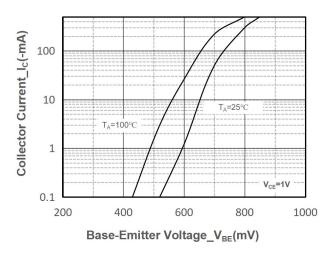
DC Current Gain vs. Collector Current

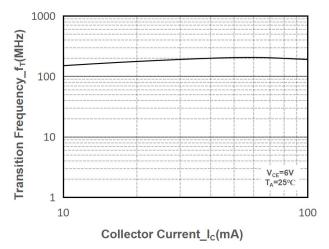




V_{BE(sat)} vs. Collector Current

V_{CE(sat)} vs. Collector Current





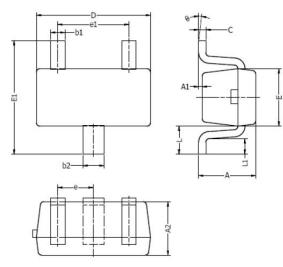
Collector Current vs. Base-Emitter Voltage

Transition Frequency vs. Collector Current

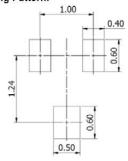


Package Information

SOT-523



Typical	Soldering	Pattern:



DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
Α	0.70	0.90	0.028	0.035
A1	0.00	0.10	0.000	0.004
A2	0.70	0.80	0.028	0.031
b1	0.15	0.25	0.006	0.010
b2	0.25	0.35	0.010	0.014
С	0.10	0.20	0.004	0.008
D	1.50	1.70	0.059	0.067
E	0.70	0.90	0.028	0.035
E1	1.45	1.75	0.057	0.069
е	0.50 TYP.		0.020	TYP.
e1	0.90	1.10	0.035	0.043
L	0.40 REF.		0.016	REF.
L1	0.10	0.30	0.004	0.012
θ	0 °	8°	O°	8°

NOTES:

- Above package outline conforms to JEITA EAIJ ED-7500A SC-75A.
 Dimensions are exclusive of Burrs, Mold Flash & Tie Bar extrusions.



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